

B. In the Claims:

Please amend the claims as follows:

1. (currently amended) An etching method configured to make a through hole by etching an object ~~to be etched~~ from ~~one of major surfaces~~ a surface thereof by dry etching, comprising:

~~said the~~ dry etching being conducted under the condition where a conductor with a higher electric conductivity than that of ~~said an~~ entity is in contact with ~~said the~~ entity at least in or near a location for making ~~said the~~ through hole; and

wherein the through hole is made by setting the conductor with a high melting point on a wafer stage in a dry etching apparatus; maintaining the wafer stage at a temperature above the melting point of the conductor to melt the conductor and putting a wafer as the entity thereon; and hereunder conducting the dry etching of the wafer.

2. (currently amended) The etching method according to claim 1 wherein ~~said the~~ entity to be etched is made of a semiconductor.

3. (currently amended) The etching method according to claim 1 wherein ~~said the~~ entity to be etched is made of silicon.

4. (currently amended) The etching method according to claim 1 wherein ~~said the~~ conductor is a metal.

5. (currently amended) The etching method according to claim 1 wherein ~~said the~~ conductor is a conductor film formed on the entire surface of ~~said the~~ other surface of said the entity to be etched.

6. (currently amended) The etching method according to claim 1 wherein ~~said the~~ conductor is a conductor film formed on a location of ~~said the~~ other surface of said the entity near the region for making ~~said the~~ through hole.

7. (currently amended) The etching method according to claim 1 wherein ~~said~~ the conductor is a metal. ~~having a low melting point.~~

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8. (currently amended) The etching method according to claim 1 wherein ~~said~~ the through hole is made by setting ~~said~~ the conductor with a ~~low~~ melting point on a wafer stage in a dry etching apparatus; maintaining ~~said~~ the wafer stage at a temperature above ~~not lower than~~ the melting point of ~~said~~ the conductor to melt ~~said~~ the conductor and putting a wafer as ~~said~~ the entity thereon; fixing ~~said~~ the wafer onto ~~said~~ the wafer stage by lowering temperature of ~~said~~ the wafer stage to a level lower than the melting point of ~~said~~ the conductor, and thereafter conducting ~~said~~ the dry etching of ~~said~~ the wafer.

☒ 9. Cancel.

10. (currently amended) The etching method according to claim 1 wherein ~~said~~ the dry etching is conducted by using SF₆ gas and C₄F₈ gas.

11. (currently amended) The etching method according to claim 1 wherein ~~said~~ the dry etching uses ions.

12. (currently amended) The etching method according to claim 1 wherein ~~said~~ the dry etching is reactive ion etching.

A3
13. (currently amended) The etching method according to claim 1 wherein ~~said~~ the through hole has an aspect ratio not smaller than 3.

14. (currently amended) The etching method according to claim 1 wherein ~~said~~ the through hole has an aspect ratio not smaller than 5.

15. (currently amended) The etching method according to claim 1 wherein ~~said~~ the through hole has an aspect ratio not smaller than 8.

16. (currently amended) The etching method according to claim 1 wherein ~~said~~ the through hole has an aspect ratio not smaller than 10.

17. (currently amended) A manufacturing method of a structure including a step of making a through hole by etching an object ~~to be etched~~ from ~~one of major surfaces~~ a surface thereof by dry etching, comprising:

said the dry etching being conducted under the condition where a conductor with a higher electric conductivity than that of ~~said entity~~ a silicon semiconductor is in contact with ~~said entity~~ the silicon semiconductor at least in or near a location for making ~~said the~~ through hole.

[18. to 19. Canceled.]

20. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ conductor is a metal.

21. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ conductor is a conductor film formed on the entire surface of ~~said the~~ other surface of ~~said the~~ entity to be etched.

22. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ conductor is a conductor film formed on a location of ~~said the~~ other surface of ~~said the~~ entity near the region for making ~~said the~~ through hole.

23. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ conductor is a metal. ~~having a low melting point.~~

24. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ through hole is made by setting ~~said the~~ conductor with a ~~low~~ melting point on a wafer stage in a dry etching apparatus; maintaining ~~said the~~ wafer stage at a temperature above ~~not lower than~~ the melting point of ~~said the~~ conductor to melt ~~said the~~ conductor and putting a wafer as ~~said the~~ entity thereon; fixing ~~said the~~ wafer onto ~~said the~~ wafer stage by lowering temperature of ~~said the~~ wafer stage to a level lower than the melting point of ~~said the~~ conductor, and thereafter conducting ~~said the~~ dry etching of ~~said the~~ wafer.

25. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ through hole is made by setting ~~said the~~ conductor with a ~~high~~ melting point on a wafer stage in a dry etching apparatus; maintaining ~~said the~~ wafer stage at a temperature above ~~not~~ ~~lower than~~ the melting point of ~~said the~~ conductor to melt ~~said the~~ conductor and putting a wafer as ~~said the~~ entity thereon; and hereunder conducting ~~said the~~ dry etching of ~~said the~~ wafer.

26. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ dry etching is conducted by using SF₆ gas and C₄F₈ gas.

Amended 27. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ dry etching uses ions.

28. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ dry etching is reactive ion etching.

29. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ through hole has an aspect ratio not smaller than 3.

30. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ through hole has an aspect ratio not smaller than 5.

31. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ through hole has an aspect ratio not smaller than 8.

32. (currently amended) The manufacturing method of a structure according to claim 17 wherein ~~said the~~ through hole has an aspect ratio not smaller than 10.

33. (new) A manufacturing method of a structure including a step of making a through hole by etching an object to be etched from one of major surfaces thereof by dry etching, comprising:

AS the dry etching being conducted under the condition where a conductor with a higher electric conductivity than that of the entity is in contact with the entity at least in or near a location for making the through hole; and

wherein the through hole is made by setting the conductor with a high melting point on a wafer stage in a dry etching apparatus; maintaining the wafer stage at a temperature above the melting point of the conductor to melt the conductor and putting a wafer as the entity thereon; and hereunder conducting the dry etching of the wafer.

34. (new) The manufacturing method of claim 33, wherein the dry etching is conducted by using SF_6 gas and C_4F_8 gas.

35. (new) The manufacturing method of claim 33, wherein the dry etching uses ions.

36. (new) The manufacturing method of claim 33, wherein the dry etching is reactive ion etching.

37. (new) The manufacturing method of claim 33, wherein the through hole has an aspect ratio not smaller than 3.

38. (new) The manufacturing method of claim 33, wherein the through hole has an aspect ratio not smaller than 5.

39. (new) The manufacturing method of claim 33, wherein the through hole has an aspect ratio not smaller than 8.

40. (new) The manufacturing method of claim 33, wherein the through hole has an aspect ratio not smaller than 10.